

Product data sheet

Product profile

1.1 General description

The BFT25A is a silicon NPN transistor, primarily intended for use in RF low power amplifiers, such as pocket telephones and paging systems with signal frequencies up to 2 GHz.

The transistor is encapsulated in a 3-pin plastic SOT23 envelope.

1.2 Features and benefits

- Low current consumption (100 μA to 1 mA)
- Low noise figure
- Gold metallization ensures excellent reliability.

1.3 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|------------------|-------------------------------------|---|------------|-----|-----|-----|------|
| V_{CBO} | collector-base voltage | open emitter | | - | - | 8 | V |
| V _{CEO} | collector-emitter voltage | open base | | - | - | 5 | V |
| I _C | DC collector current | | | - | - | 6.5 | mA |
| P _{tot} | total power dissipation | up to $T_s = 165 ^{\circ}\text{C}$ | <u>[1]</u> | - | - | 32 | mW |
| h _{FE} | DC current gain | $I_C = 0.5 \text{ mA}; V_{CE} = 1 \text{ V}$ | | 50 | 80 | 200 | |
| f _T | transition frequency | $I_{C} = 1 \text{ mA}; V_{CE} = 1 \text{ V};$ $T_{amb} = 25 \text{ °C};$ f = 500 MHz | | 3.5 | 5 | - | GHz |
| G _{UM} | maximum unilateral power gain | $I_C = 0.5 \text{ mA}; V_{CE} = 1 \text{ V};$ $T_{amb} = 25 ^{\circ}\text{C};$ f = 1 GHz | | - | 15 | - | dB |
| F | noise figure | $\Gamma = \Gamma_{\text{opt}}$; $I_{\text{C}} = 0.5 \text{ mA}$; $V_{\text{CE}} = 1 \text{ V}$; $T_{\text{amb}} = 25 ^{\circ}\text{C}$; $f = 1 \text{ GHz}$ | | - | 1.8 | - | dB |
| | | $\begin{split} &\Gamma = \Gamma_{opt}; \ I_C = 1 \ mA; \\ &V_{CE} = 1 \ V; \\ &T_{amb} = 25 \ ^{\circ}C; \ f = 1 \ GHz \end{split}$ | | - | 2 | - | dB |

^[1] T_s is the temperature at the soldering point of the collector tab.



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2. Pinning information

Table 2. Discrete pinning

| Pin | Description | Simplified outline | Symbol | |
|-----------|-------------|--------------------|--------|--|
| Code: V10 | | | | |
| 1 | base | | 3 I | |
| 2 | emitter | | 1 — | |
| 3 | collector | 1 2 | ' | |
| | | | 2 | |
| | | | sym021 | |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|--|---------|
| | Name | Description | Version |
| BFT25A | - | plastic surface mounted package; 3 leads | SOT23 |

4. Marking

Table 4. Marking

| Type number | Marking code ^[1] |
|-------------|-----------------------------|
| BFT25A | 34* |

[1] * = p: Made in Hong Kong.

* = t : Made in Malaysia.

* = W : Made in China.

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------|-----------------------------|-------|------|------|
| V_{CBO} | collector-base voltage | open emitter | - | 8 | V |
| V_{CEO} | collector-emitter voltage | open base | - | 5 | V |
| V _{EBO} | emitter-base voltage | open collector | - | 2 | V |
| I _C | DC collector current | | - | 6.5 | mA |
| P _{tot} | total power dissipation | up to $T_s = 165 ^{\circ}C$ | [1] - | 32 | mW |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | - | 175 | °C |
| <u>'</u> | | | | | |

^[1] T_s is the temperature at the soldering point of the collector tab.

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6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Тур | Unit |
|---------------|----------------------------------|------------|----------------|------|
| $R_{th(j-s)}$ | from junction to soldering point | | <u>[1]</u> 260 | K/W |

^[1] T_s is the temperature at the soldering point of the collector tab.

7. Characteristics

Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|-------------------------------------|---|-------|-----|------|------|
| I_{CBO} | collector cut-off current | $I_E = 0 \text{ A}; V_{CB} = 5 \text{ V}$ | - | - | 50 | nA |
| h_{FE} | DC current gain | $I_C = 0.5 \text{ mA}; V_{CE} = 1 \text{ V}$ | 50 | 80 | 200 | |
| f _T | transition frequency | $I_{C} = 1 \text{ mA}; V_{CE} = 1 \text{ V};$ $T_{amb} = 25 ^{\circ}\text{C};$ f = 500 MHz | 3.5 | 5 | - | GHz |
| C _{re} | feedback capacitance | $I_C = I_c = 0 A; V_{CB} = 1 V;$ f = 1 MHz | - | 0.3 | 0.45 | pF |
| G _{UM} | maximum unilateral power gain | $I_{C} = 0.5 \text{ mA}; V_{CE} = 1 \text{ V};$ $T_{amb} = 25 ^{\circ}\text{C}; f = 1 \text{ GHz}$ | [1] - | 15 | - | dB |
| F | noise figure | $\begin{split} \Gamma &= \Gamma_{\text{opt}}; \ I_{\text{C}} = 0.5 \ \text{mA}; \\ V_{\text{CE}} &= 1 \ \text{V}; \\ T_{\text{amb}} &= 25 \ ^{\circ}\text{C}; \ f = 1 \ \text{GHz} \end{split}$ | - | 1.8 | - | dB |
| | | $\Gamma = \Gamma_{opt}$; $I_C = 1$ mA; $V_{CE} = 1$ V; $T_{amb} = 25$ °C; $f = 1$ GHz | - | 2 | - | dB |

^[1] $\;\;$ G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and

$$G_{\text{UM}} = 10 \log \frac{\left|S_{21}\right|^2}{(I - \left|S_{11}\right|^2)(I - \left|S_{22}\right|^2)} dB$$

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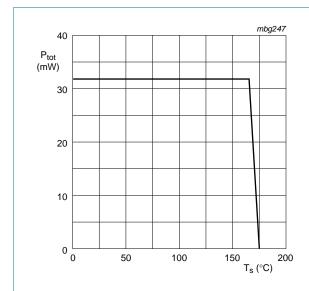
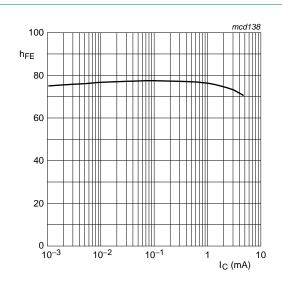


Fig 1. Power derating curve.



 $V_{CE} = 1 V.$

Fig 2. DC current gain as a function of collector current.

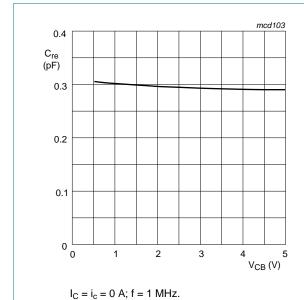
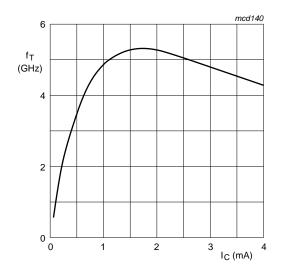


Fig 3. Feedback capacitance as a function of collector-base voltage.

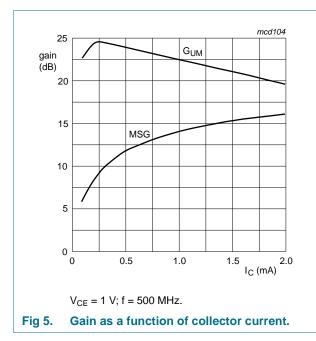


 V_{CE} = 1 V; T_{amb} = 25 °C; f = 500 MHz.

Fig 4. Transition frequency as a function of collector current.

Figure 5, 6, 7 and 8, G_{UM} = maximum unilateral power gain; MSG = maximum stable gain.

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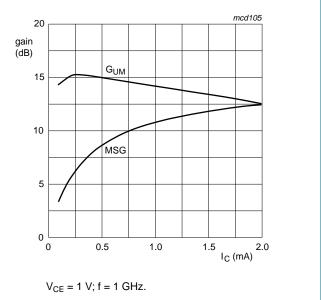
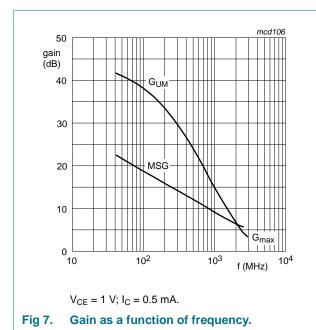


Fig 6. Gain as a function of collector current.



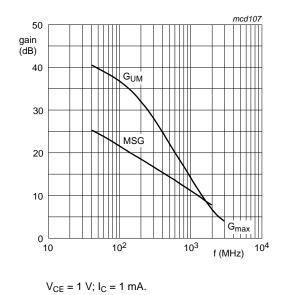


Fig 8. Gain as a function of frequency.

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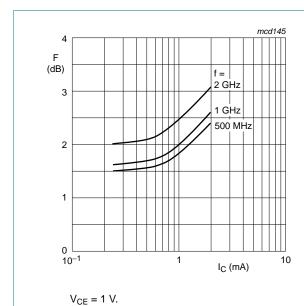


Fig 9. Minimum noise figure as a function of collector current.

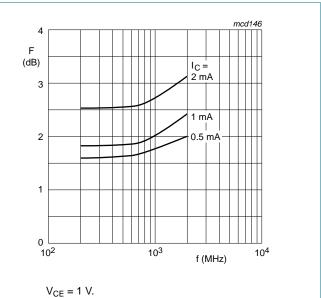


Fig 10. Minimum noise figure as a function of frequency.

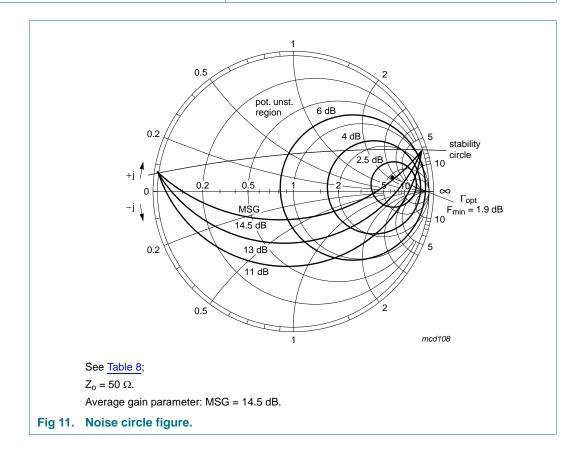


Table 8. Noise parameters

| f (MHz) | V _{CE} (V) | I _C (mA) | F _{min} (dB) | $\Gamma_{ m opt}$ | | R _n /50 |
|---------|---------------------|---------------------|-----------------------|-------------------|-------|--------------------|
| | | | | (mag) | (ang) | |
| 500 | 1 | 1 | 1.9 | 0.79 | 4 | 2.5 |

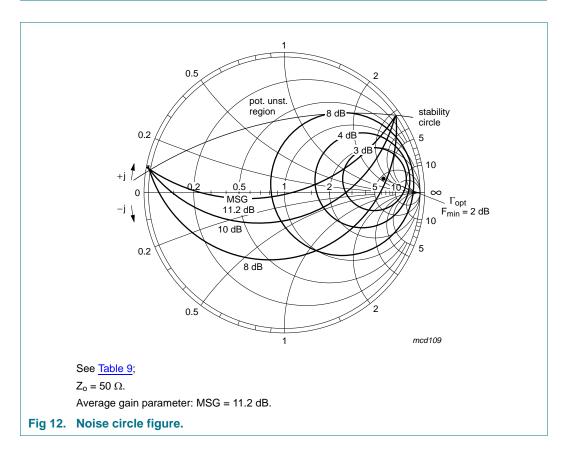


Table 9. Noise parameters

| f (MHz) | V _{CE} (V) | I _C (mA) | F _{min} (dB) | Γ_{opt} | | R _n /50 |
|---------|---------------------|---------------------|-----------------------|----------------|-------|--------------------|
| | | | | (mag) | (ang) | |
| 1000 | 1 | 1 | 2 | 0.74 | 8 | 2.6 |

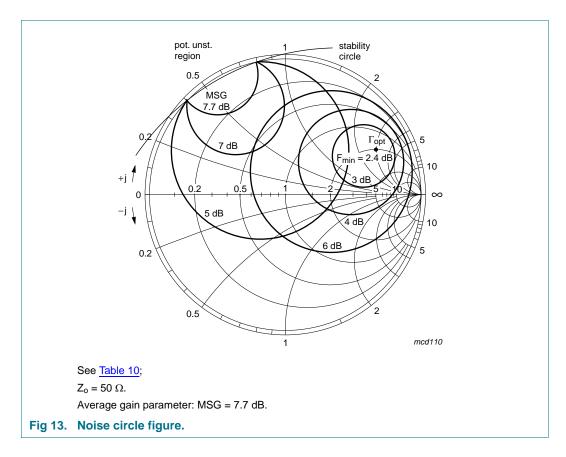
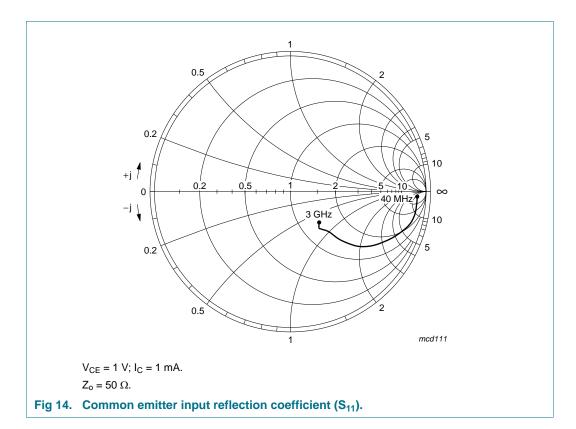
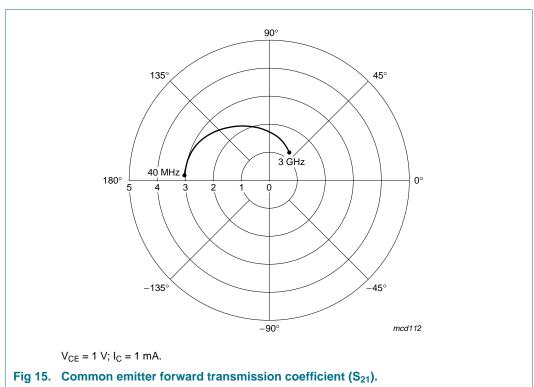
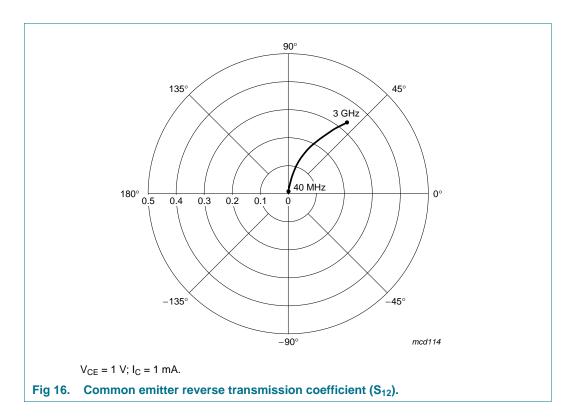


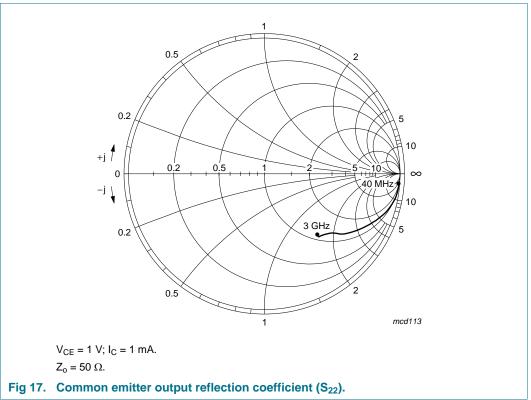
Table 10. Noise parameters

| f (MHz) | V _{CE} (V) | I _C (mA) | F _{min} (dB) | Γ_{opt} | | R _n /50 |
|---------|---------------------|---------------------|-----------------------|----------------|-------|--------------------|
| | | | | (mag) | (ang) | |
| 2000 | 1 | 1 | 2.4 | 0.72 | 26 | 1.7 |









8. Package outline

Plastic surface-mounted package; 3 leads SOT23 В Α Χ = v M A 3 **→** | w (M) B е detail X 0 1 2 **DIMENSIONS (mm are the original dimensions)** UNIT D Ε Q e₁ H_{E} L_p w max. 0.48 0.45 1.1 0.15 3.0 1.4 0.55 0.1 0.9 0.38 0.09 2.8 1.2 0.15

Fig 18. Package outline.

OUTLINE

VERSION

SOT23

IEC

JEDEC

TO-236AB

ISSUE DATE

-04-11-04

06-03-16

EUROPEAN

PROJECTION

JEITA

REFERENCES

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9. Revision history

Table 11. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes | |
|--------------------------------|---|-----------------------------|---------------------------|----------------|--|
| BFT25A v.5 | 20110912 | Product data sheet | - | BFT25A v.4 | |
| Modifications: | The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. | | | | |
| | Package or | utline drawings have been u | pdated to the latest vers | sion. | |
| BFT25A v.4 (9397 750 13399) | 20040706 | Product data sheet | - | BFT25A_CNV v.3 | |
| BFT25A_CNV v.3 | 19971205 | Product specification | - | - | |
| | | | | | |

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10. Legal information

10.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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